

2SA2078G

Silicon PNP epitaxial planar type

For general amplification Complementary to 2SC5846G

■ Features

- High forward current transfer ratio h_{FE}
- SSS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V_{CBO}	-60	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Emitter-base voltage (Collector open)	V_{EBO}	-7	V	
Collector current	I_{C}	-100	mA	
Peak collector current	I_{CP}	-200	mA	
Collector power dissipation	P _C	100	mW	
Junction temperature	Tj	125	°CO	
Storage temperature	T _{stg}	-55 to +125	°C	

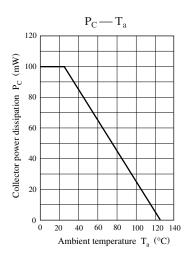
Package

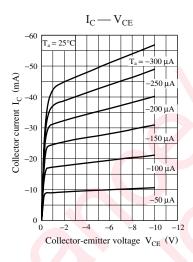
- Code SSSMini3-F2
- Marking Symbol: 7H
- Pin Name
 - 1. Base
 - 2. Emitter
 - 3. Collector

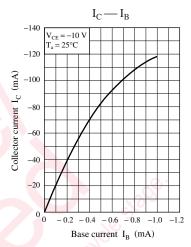
■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

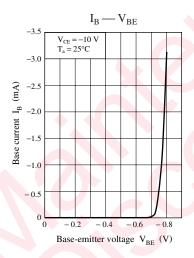
Symbol	Conditions	Min	Тур	Max	Unit
V _{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-60	350		V
V _{CEO}	$I_{\rm C} = -100 \ \mu {\rm A}, \ I_{\rm B} = 0$	-50	O		V
V_{EBO}	$I_E = -10 \mu A, I_C = 0$	-7			V
I_{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
I _{CEO}	$V_{CE} = -10 \text{ V}, I_B = 0$			-100	μΑ
h _{FE}	$V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$	180		390	_
V _{CE(sat)}	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		- 0.2	- 0.5	V
f_T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
C_{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2.2		pF
	$\begin{array}{c} V_{CBO} \\ V_{CEO} \\ V_{EBO} \\ I_{CBO} \\ I_{CEO} \\ h_{FE} \\ V_{CE(sat)} \\ f_T \end{array}$	$\begin{split} &V_{CBO} &I_{C} = -10 \ \mu A, \ I_{E} = 0 \\ &V_{CEO} &I_{C} = -100 \ \mu A, \ I_{B} = 0 \\ &V_{EBO} &I_{E} = -10 \ \mu A, \ I_{C} = 0 \\ &I_{CBO} &V_{CB} = -20 \ V, \ I_{E} = 0 \\ &I_{CEO} &V_{CE} = -10 \ V, \ I_{B} = 0 \\ &h_{FE} &V_{CE} = -10 \ V, \ I_{C} = -2 \ mA \\ &V_{CE(sat)} &I_{C} = -100 \ mA, \ I_{B} = -10 \ mA \\ &f_{T} &V_{CB} = -10 \ V, \ I_{E} = 1 \ mA, \ f = 200 \ MHz \end{split}$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

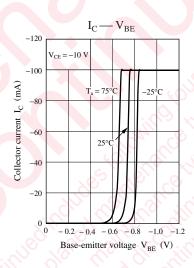
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

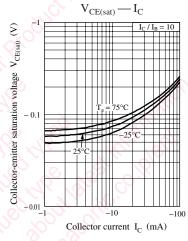


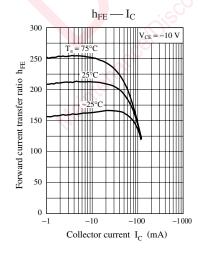


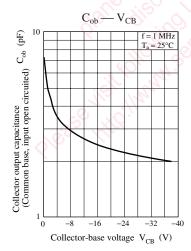


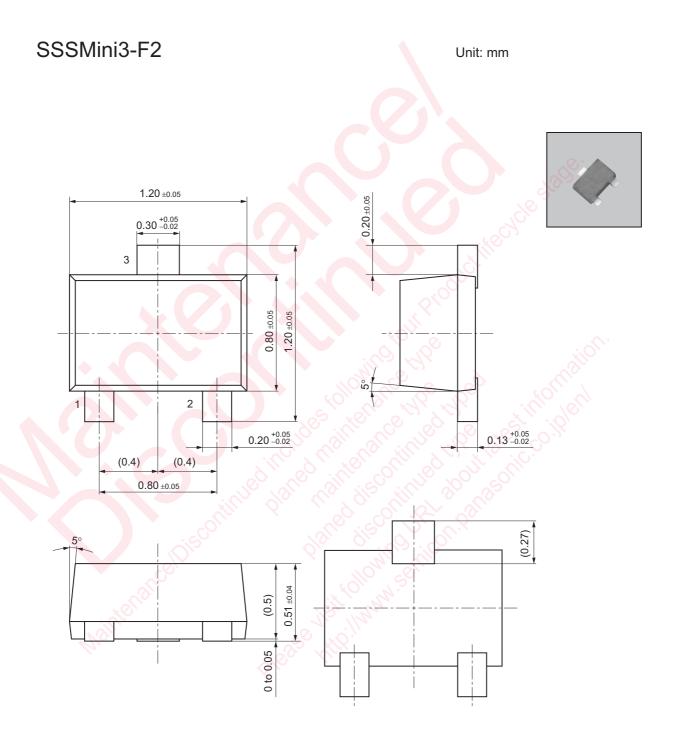












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